

Sadhvikas Addamane

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	A Tunable Unidirectional Source for GUSTO™s Local Oscillator at 4.74 THz. IEEE Transactions on Terahertz Science and Technology, 2022, 12, 144-150.	3.1	8
2	Terahertz Pulse Generation from GaAs Metasurfaces. ACS Photonics, 2022, 9, 1136-1142.	6.6	20
3	Submonolayer Quantum-Dot Based Saturable Absorber for Femtosecond Pulse Generation. Journal of Electronic Materials, 2021, 50, 2710-2715.	2.2	2
4	Manipulation of quantum dot emission with semiconductor metasurfaces exhibiting magnetic quadrupole resonances. Optics Express, 2021, 29, 5567.	3.4	6
5	Highly efficient terahertz photoconductive metasurface detectors operating at microwatt-level gate powers. Optics Letters, 2021, 46, 3159.	3.3	12
6	Controllable finite ultra-narrow quality-factor peak in a perturbed Dirac-cone band structure of a photonic-crystal slab. Applied Physics Letters, 2021, 119, .	3.3	6
7	Multi-mode lasing in terahertz metasurface quantum-cascade VECSELS. Applied Physics Letters, 2021, 119, 111103.	3.3	3
8	Tunable quantum-cascade VECSEL operating at 1.9 THz. Optics Express, 2021, 29, 34695.	3.4	7
9	THz time-domain characterization of amplifying quantum-cascade metasurface. Applied Physics Letters, 2021, 119, .	3.3	6
10	Thin THz QCL active regions for improved continuous-wave operating temperature. AIP Advances, 2021, 11, .	1.3	10
11	InGaSb Defect Filter Layer to Improve Performance of GaSb Solar Cells Grown on GaAs Substrates. Journal of Electronic Materials, 2020, 49, 7153-7158.	2.2	3
12	Perfectly absorbing dielectric metasurfaces for photodetection. APL Photonics, 2020, 5, .	5.7	33
13	A transmission electron microscopy study of dislocation propagation and filtering in highly mismatched GaSb/GaAs heteroepitaxy. Journal of Applied Physics, 2020, 128, 225301.	2.5	2
14	Epitaxial Regrowth and Hole Shape Engineering for Photonic Crystal Surface Emitting Lasers (PCSELS). Journal of Crystal Growth, 2020, 535, 125531.	1.5	12
15	Perfect absorption in GaAs metasurfaces near the bandgap edge. Optics Express, 2020, 28, 35284.	3.4	15
16	Revealing Temperature-Dependent Absorption and Emission Enhancement Factors in Plasmon Coupled Semiconductor Heterostructures. ACS Applied Electronic Materials, 2019, 1, 1439-1448.	4.3	4
17	InAs FinFETs Performance Enhancement by Superacid Surface Treatment. IEEE Transactions on Electron Devices, 2019, 66, 1856-1861.	3.0	10
18	Optically Pumped 1.4µm Low Threshold Photonic Crystal Surface Emitting Lasers Grown on GaAs Substrate. , 2019, , .		2

#	ARTICLE	IF	CITATIONS
19	Interplay between total thickness and period thickness in the phonon thermal conductivity of superlattices from the nanoscale to the microscale: Coherent versus incoherent phonon transport. Physical Review B, 2018, 97, .	3.2	48
20	High-Speed InP-Based p-i-n Photodiodes With InGaAs/GaAsSb Type-II Quantum Wells. IEEE Photonics Technology Letters, 2018, 30, 399-402.	2.5	11
21	Experimental Evidence of Suppression of Subterahertz Phonons and Thermal Conductivity in GaAs/AlAs Superlattices Due to Extrinsic Scattering Processes. Journal of Physical Chemistry C, 2018, 122, 29577-29585.	3.1	5
22	Pixelated GaSb solar cells on silicon by membrane bonding. Applied Physics Letters, 2018, 113, 123502.	3.3	3
23	Modeling and experimental realization of modelocked VECSEL producing high power sub-100 fs pulses. Applied Physics Letters, 2018, 113, .	3.3	23
24	Light-Emitting Metasurfaces: Simultaneous Control of Spontaneous Emission and Far-Field Radiation. Nano Letters, 2018, 18, 6906-6914.	9.1	126
25	InP-Based Waveguide-Integrated Photodiodes With InGaAs/GaAsSb Type-II Quantum Wells and 10-GHz Bandwidth at 2 μ m Wavelength. Journal of Lightwave Technology, 2018, 36, 4981-4987.	4.6	14
26	Multi-Angle VECSEL Cavities for Dispersion Control and Peak-Power Scaling. IEEE Photonics Technology Letters, 2017, 29, 326-329.	2.5	13
27	Active Mediation of Plasmon Enhanced Localized Exciton Generation, Carrier Diffusion and Enhanced Photon Emission. Scientific Reports, 2017, 7, 864.	3.3	7
28	High-speed type-II InGaAs/GaAsSb multiple quantum-well integrated waveguide photodiodes at 2 μ m wavelength. , 2017, , .		0
29	Investigation of Surface Defects in AlInSb Metamorphic Buffer (MB) Grown on GaSb. Journal of Electronic Materials, 2016, 45, 6258-6264.	2.2	1
30	Molecular beam epitaxy of high-resistivity AlSb for room-temperature radiation detectors. , 2015, , .		0
31	Isolating GaSb Membranes Grown Metamorphically on GaAs Substrates Using Highly Selective Substrate Removal Etch Processes. Journal of Electronic Materials, 2015, 44, 1327-1331.	2.2	4
32	Growth and Optimization of 2- μ m InGaSb/AlGaSb Quantum-Well-Based VECSELs on GaAs/AlGaAs DBRs. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1700611-1700611.	2.9	4